Power MOSFETs for Industrial and Consumer

N-channel Power MOSFETs - 20V to 150V -

Selection guide 2026

Contents

No. 68AN067E Rev.001
March 2026

1. About ROHM MOSFETs

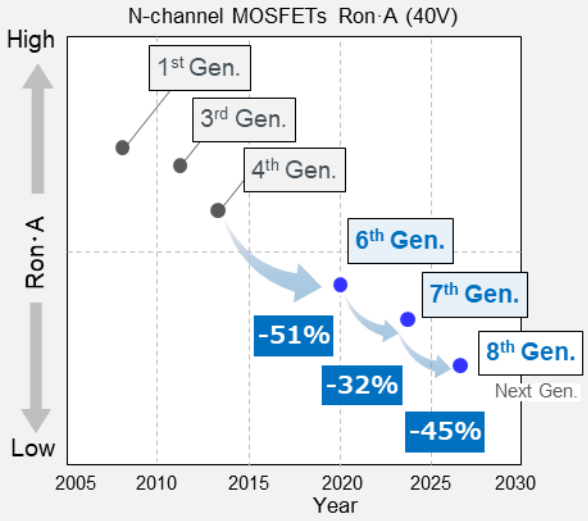
ROHM's N-channel power MOSFETs offer an extensive portfolio of 20V to 150V MOSFETs, featuring the latest packages ranging from compact packages to high-current packages—making them suitable for a wide range of applications, including power supplies, motor drives, and communication equipment.

Reduction of On-Resistance

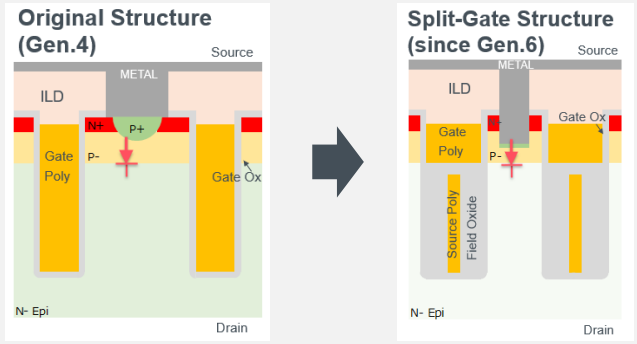
Latest Silicon Technology enabling low Ron·A

Leveraging ROHM's proprietary technologies, process scaling has been advanced to significantly improve device performance (Ron·A), enabling higher system efficiency and substantial size reduction of end products.

Ron·A Reduction with the Latest Silicon Technology



Achieving Low $R_{DS(on)}$ with a Split-Gate Structure



Advantages of the Split-Gate Structure)

Low $R_{DS(on)}$

Reduction of epitaxy layer resistance enables to achieve excellent low $R_{DS(on)}$.

Low capacitance

Reduction of drain-gate capacitance enables faster switching, making the device suitable for high-frequency operation and fast control applications.

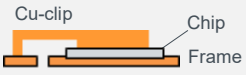
Cu-Clip Structure in a Compact, High-Thermal-Dissipation Package

Advantage 1. Low on-resistance and high current capability

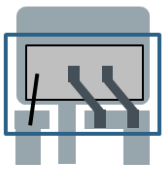
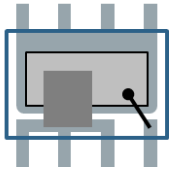
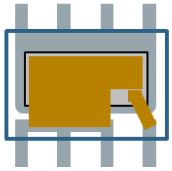
Advantage 2. Low package inductance and high-speed switching

Advantage 3. Excellent thermal performance and improved reliability

e.g.) 5.0 mm x 6.0 mm

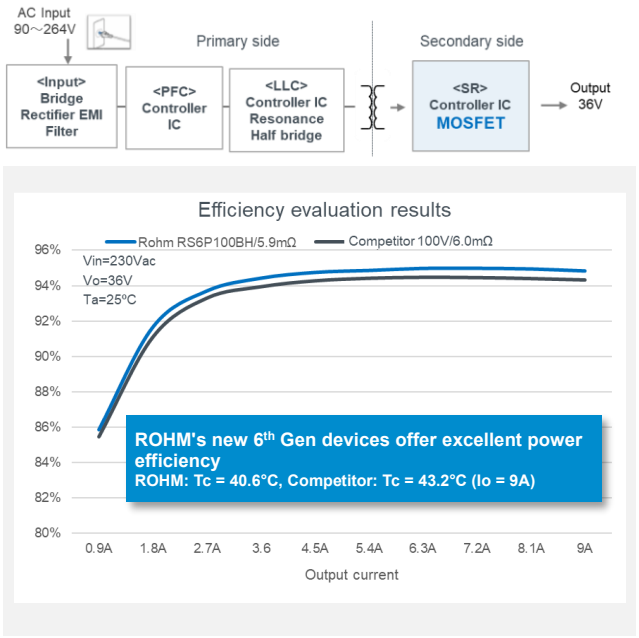


High Current / Low $R_{DS(on)}$ / High-Thermal-Dissipation

Connection	 Al-Wire	 Al-Ribbon	 **Cu-Clip**
Drain current	80A	80A	Up to **200A**
Package resistance	0.8mΩ	0.6mΩ	**0.2mΩ**

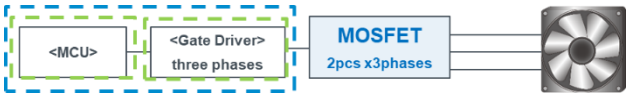
Improved efficiency in applications

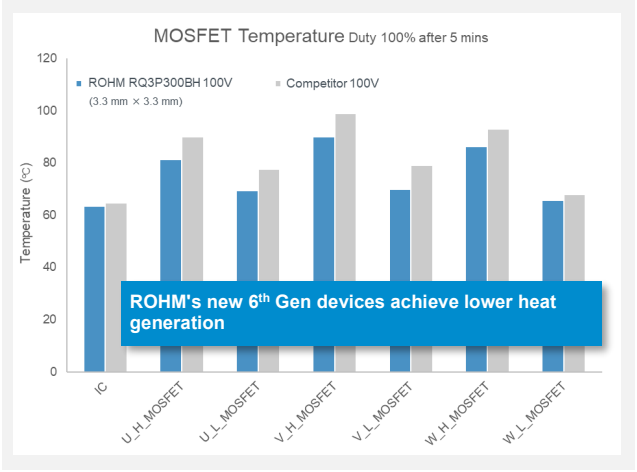
AC-DC Power Supply for Servers



ROHM's efficiency is 96.0%, while the competitor's efficiency is 95.5%.
This results in higher power efficiency compared to competing products.
*Maximum efficiency value.

Fan Motor Circuit Configuration for 48V Input

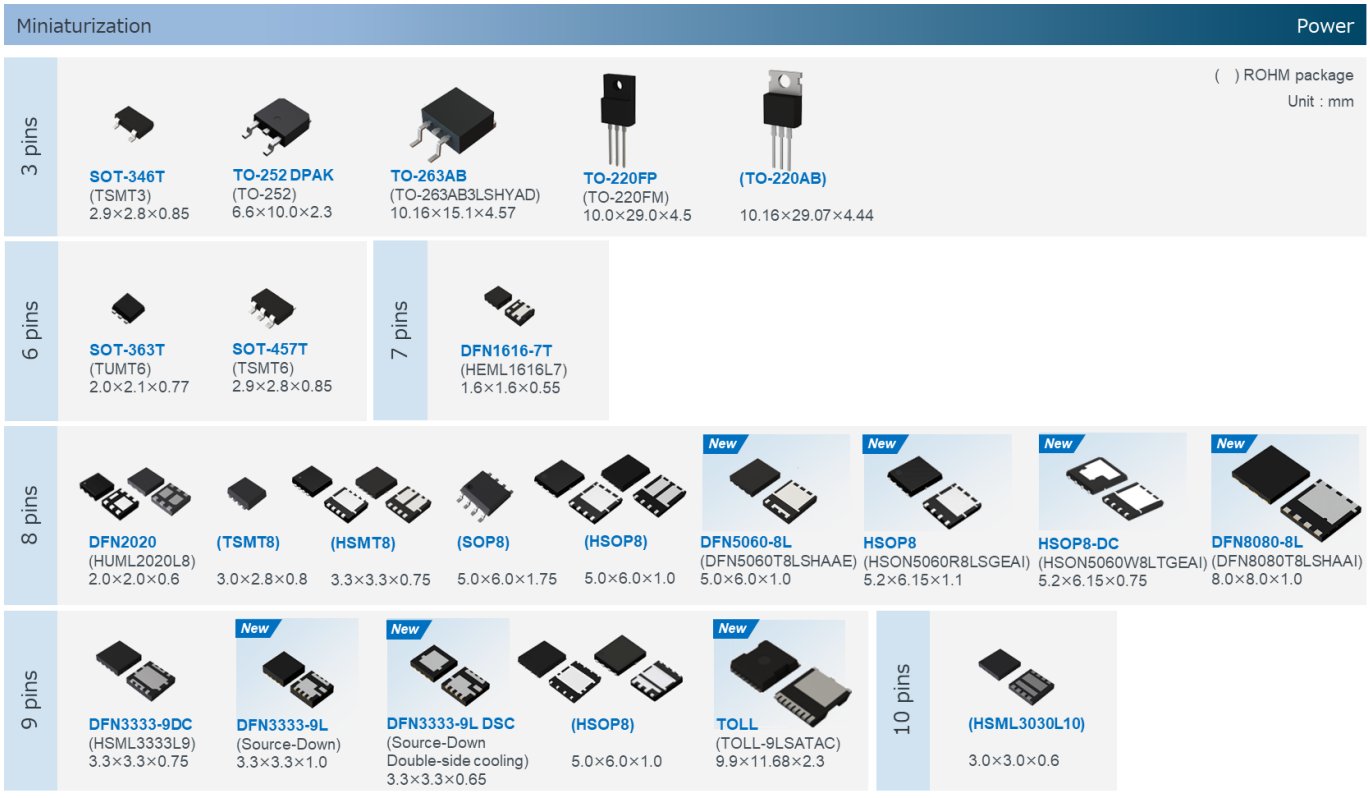




MOSFET Temperature Comparison
The average temperature of ROHM's devices is 75°C, while that of the competitor is 82°C. ROHM's new 6th Gen devices demonstrate superior thermal performance.

2. Package Lineup

ROHM is focusing on new package development, offering a wide range of packages that enhance efficiency and density in industrial equipment.



3. New Product Introduction

Wide-SOA (Safe Operating Area)

ROHM's Wide-SOA products achieve both wide SOA (conditions: V_{DS} = 48V, Pw = 1ms / 10ms) and low $R_{DS(on)}$. This enables high product reliability during hot-swap operations (power insertion while the system is powered on), while optimizing power efficiency and reducing power consumption and heat generation.

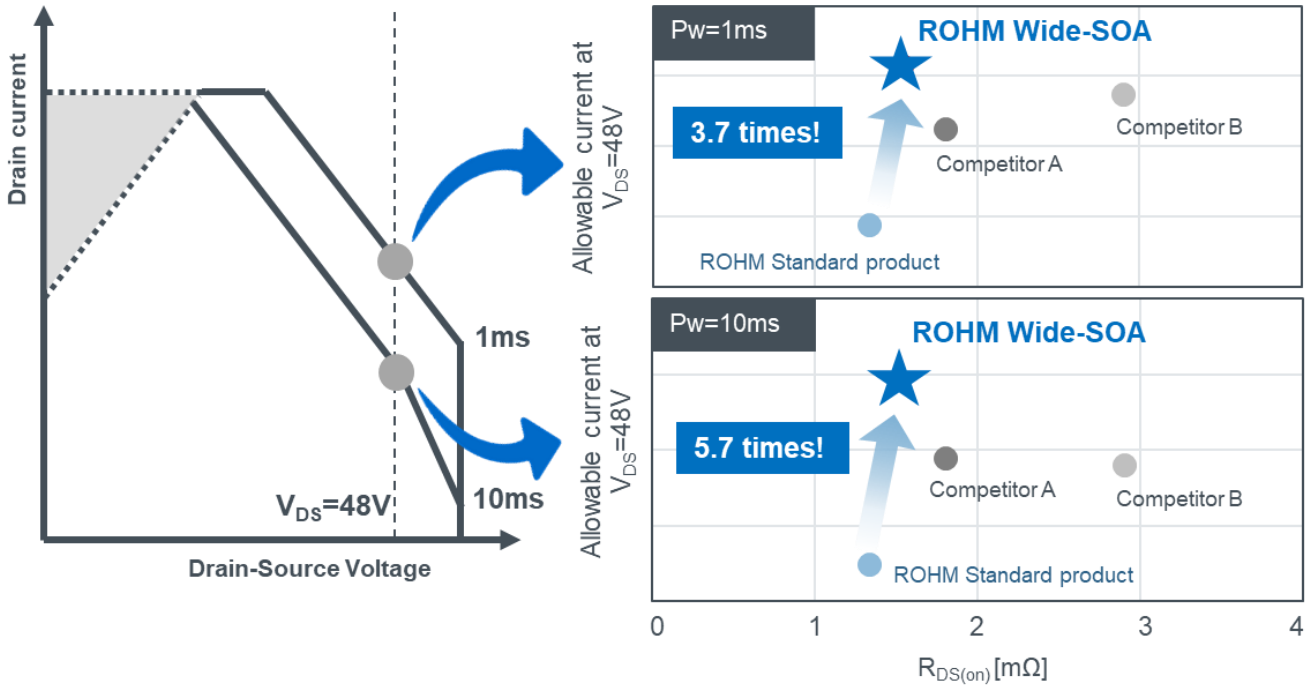
Benefits

- Wide SOA → Improved inrush current management
- Low $R_{DS(on)}$ → Improved system efficiency
- Compact / High-thermal-dissipation package → Enables stable operation

Applications

- 48V AI server systems and power supply hot-swap circuits, ORing
- 48V industrial equipment power systems (e.g. forklifts, power tools, robots, fan motors)
- AGVs (Automated Guided Vehicles), UPS and emergency power systems

Achieves wide SOA for both 1ms and 10ms pulse widths!



Products

Package	Part Number	V_{DSS} (V)	I_D (A)	$R_{DS(on)}$ Max (mΩ) V_{GS}=10V	Q_g (nC) Typ. V_{GS}=10V	C_{iss}(pF) Typ.	Drain current tolerance of SOA V_{DS}=48V (A) Pw=10ms	Drain current tolerance of SOA V_{DS}=48V (A) Pw=1ms
DFN8080-8L	RY7P250BM	100	300	**1.86**	170	11300	**16**	**50**
TOLL	RJ2P17BBM*	100	290	**2.2**	165	11300	**15.3**	**41**
DFN5060-8L	RS7P200BM	100	200	**4.0**	72	5550	**7.5**	**25**

*: Under development (specifications subject to change).

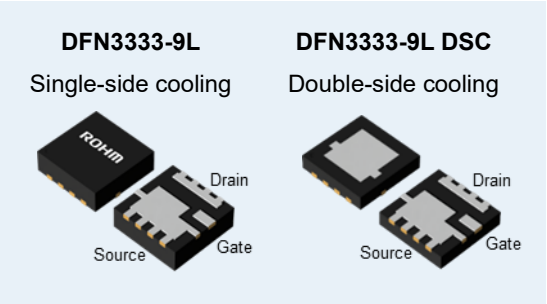
Source-Down Structure

In ROHM's source-down structure, the drain electrode—traditionally connected to the thermal pad in a drain-down configuration—is repositioned by flipping the chip upside down inside the package, allowing the source electrode to be directly connected to the thermal pad.

By combining this structure with a DFN package, a larger chip can be mounted, enabling lower $R_{DS(on)}$.
In addition, the double-side cooling package provides excellent thermal performance, contributing to higher power density and improved performance in power supply circuits.

Benefits

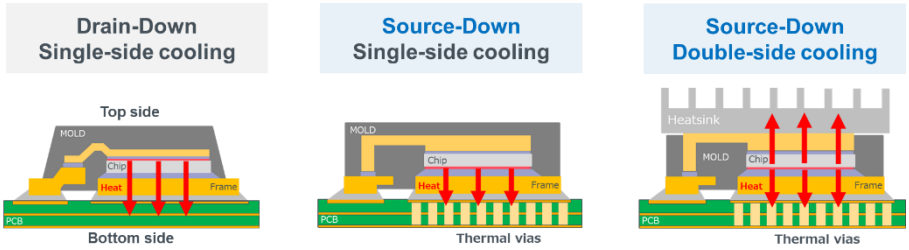
- Low $R_{DS(on)}$ in a small package
- Superior Rth(j-c) thermal performance
- Noise reduction through layout optimization



Applications

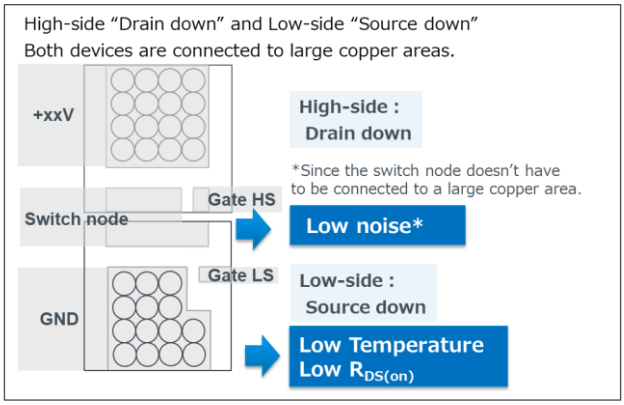
Drives, server, battery management, motor, power supply

High thermal dissipation

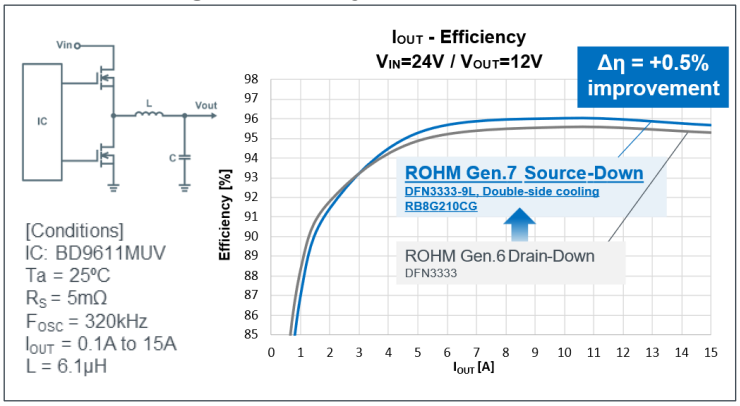


Thermal Resistance Θjc (Top side)	28.0 K/W	25.0 K/W	95% Reduction → 1.3 K/W
Thermal Resistance Θjc (Bottom side)	1.6 K/W	1.5 K/W	1.5 K/W

Noise reduction through layout optimization



Achieves high efficiency



Products

Size	Part Number		V_{DSS} (V)	I_D (A) Tc=25°C	P_D (W) Tc=25°C	$R_{DS(on)}$ Max (mΩ)			
	Single-side cooling (t=1.0mm)	Double-side cooling (t=0.65mm)				V_{GS}=10V	V_{GS}=8V	V_{GS}=6V	V_{GS}=4.5V
3.3mm x 3.3mm	RH8G210CG*	RB8G210CG*	40	210	107	1.37	-	-	2.69
	RH8G205CH*	RB8G205CH*		205	107	1.42	-	2.90	-
	RH8L130CG*	RB8L130CG*	60	130	107	3.8	-	-	7.2
	RH8L130CH*	RB8L130CH*		130	107	3.9	-	7.0	-
	RH8N105BG*	RB8N105BG*	80	105	107	5.0	-	-	8.2
	RH8N105BH*	RB8N105BH*		105	107	5.5	-	9.1	-
	RH8P085CH*	RB8P085CH*	100	85	107	7.3	9.6	-	-
	RH8R045CH*	RB8R045CH*	150	45	107	26	34	-	-

*: Under development (specifications subject to change).

High ESD tolerance

ROHM's ESD-protected MOSFETs (ESD HBM Class 1B) provide robust protection against electrostatic discharge, ensuring reliable operation in sensitive environments. Ideal for single-phase and three-phase brushless motors requiring high ESD robustness.

Available in bottom-side cooling packages for excellent heat dissipation. Additionally, dual MOSFETs reduce mounting area and component count, enabling further miniaturization and weight reduction of circuit designs.

Benefits

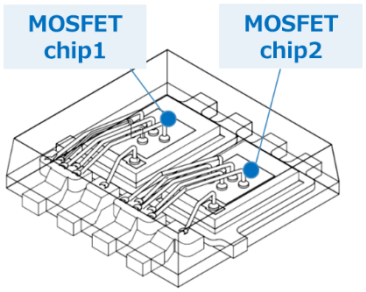
- High ESD tolerance: 800V guarantee (HBM/ Human body model)
  （Compliant with JEDEC JS-001-2023）
- High-thermal-dissipation symmetrical bottom-side cooling design
- Able to reduce mounting area and number of components compared to use of two single type MOSFETs .

Applications

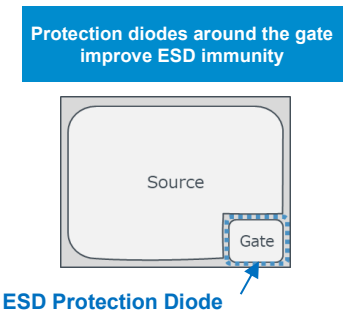
Motor application、48V industrial power supply

Built-in ESD Protection Diode

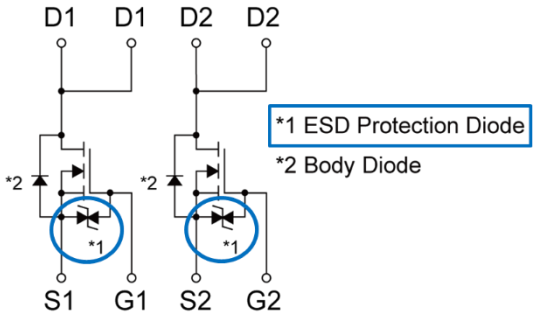
Internal structure



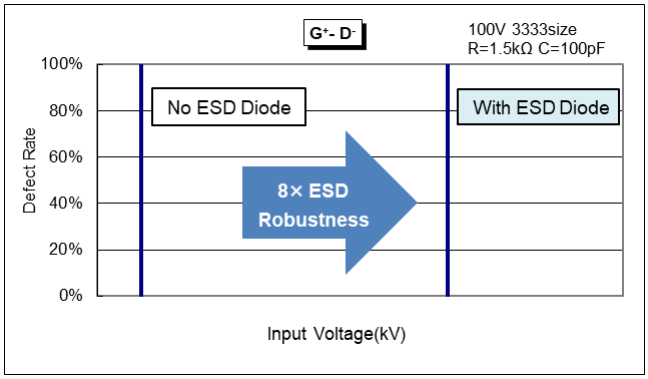
Top view of chip



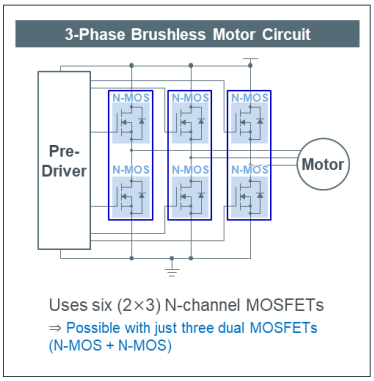
Inner circuit

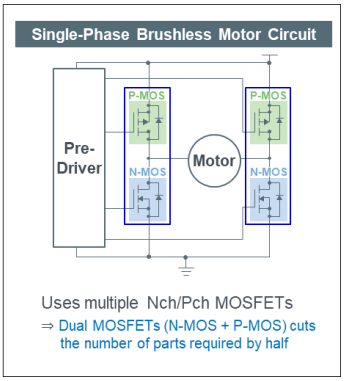


800V Rating Ensures High Reliability



Smaller Footprint & Fewer Components





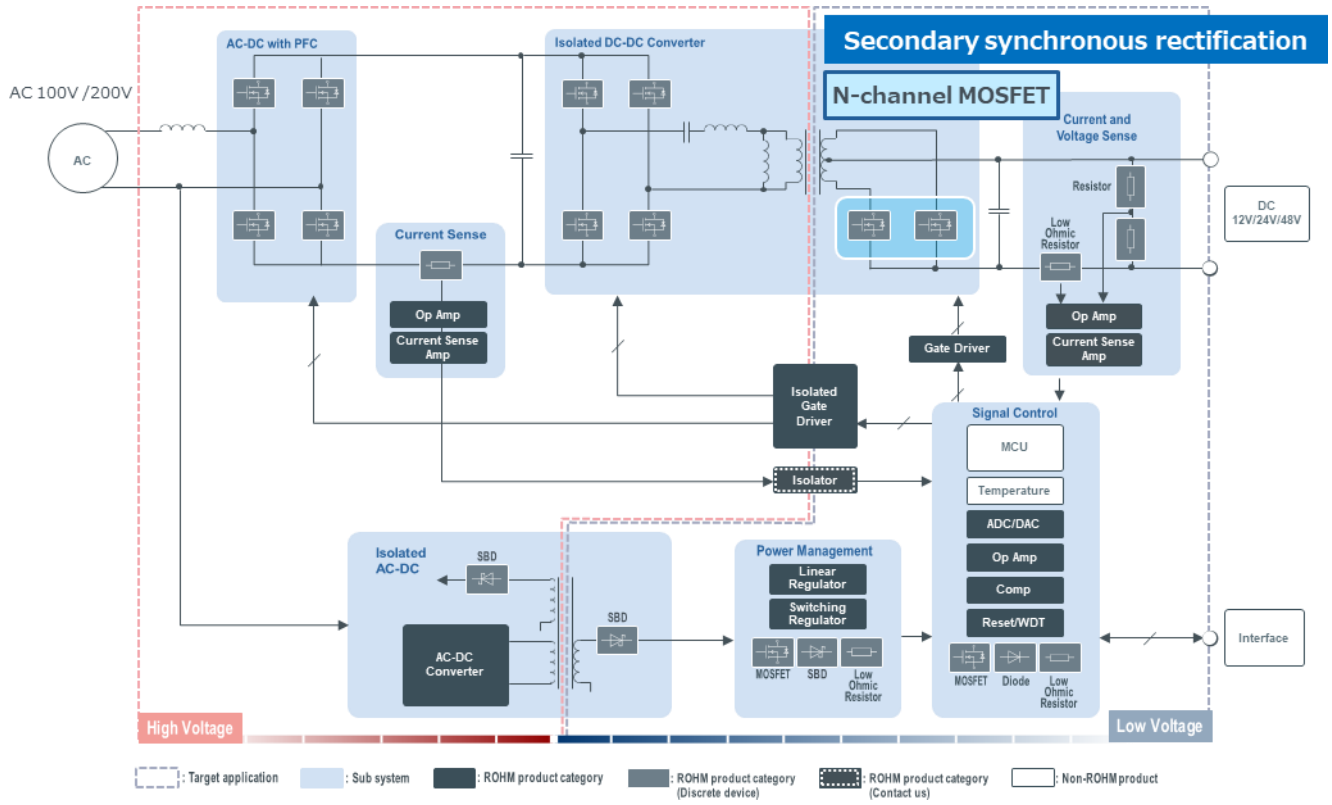
Products

Package	Polarity	Part Number	V_{DSS} (V)	I_D (A) Tc=25°C	P_D (W) Tc=25°C	$R_{DS(on)}$ Max (mΩ)			ESD (HBM)
						V_{GS}=10V	V_{GS}=6V	V_{GS}=4.5V	
HSMT8 3.3 x 3.3 x 0.75mm	N-ch ×2	HT8KE6D*	100	12.5	14	60	88	-	800V
HSOP8 5.0 x 6.0 x 1.0mm	N-ch ×2	HP8KC5D*	60	12	20	90	-	139	
	N	HP8MC5D*	60	12	20	90	-	139	
	P		-60	-12		96	-	107	

*: Under development (specifications subject to change).

4. Recommended N-channel MOSFETs by Application

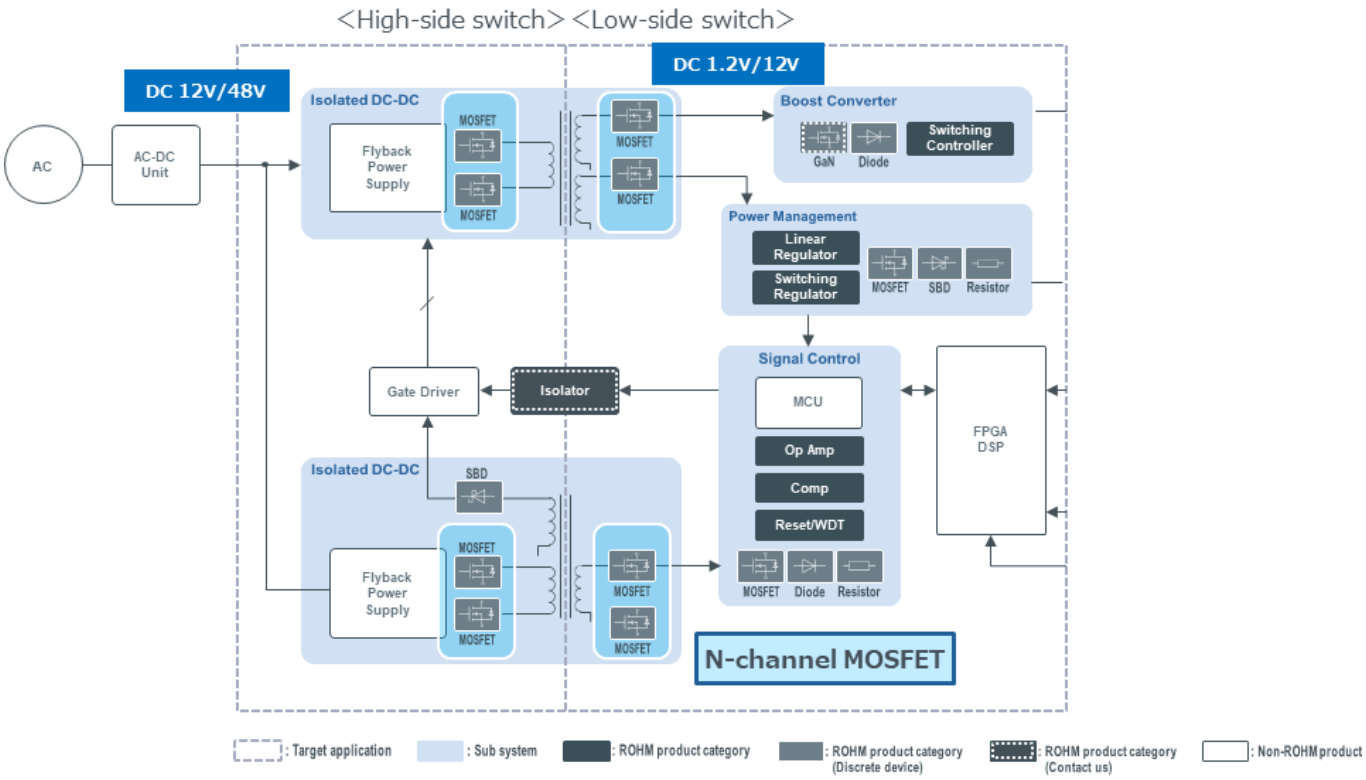
Server / Industrial AC/DC converter



Recommended N-channel MOSFETs									
Secondary synchronous rectification									
Battery Voltage	Part Number	V_{DSS} (V)	I_D (A) Silicon limit	$R_{DS(on)}$ max. V_{GS}=10V (mΩ)	Q_g V_{GS}=4.5V, 6V*, 8V**	$V_{GS(th)}$	C_{iss} Typ.	C_{oss} Typ.	Size (mm)
12V system	RS7E200BG	30	390	0.67	60	1.0 — 2.5	9500	4390	5.0 x 6.0 x 1.0 DFN5060-8L (RS7xxxxxx)
	RS7G200CG	40	410	0.64	63	1.0 — 2.5	9150	3770	
	RS6L120BG	60	150	2.7	25	1.0 — 2.5	3520	820	
24V system	RS7G200CG	40	410	0.64	63	1.0 — 2.5	9150	3770	
	RS6G120BG	40	210	1.34	34	1.0 — 2.5	4240	1950	
	RS6L120BG	60	150	2.7	25	1.0 — 2.5	3520	820	
48V system	RS7N200BH	80	230	2.0	45*	2.0 — 4.0	6550	1440	HSOP8 (RS6xxxxxx)
	RS6N120BH	80	135	3.3	33*	2.0 — 4.0	3420	1020	
	RS7P150BH	100	150*	3.8	47*	2.0 — 4.0	4740	960	
	RS7R125CH	150	125*	8.3	40**	2.0 — 4.0	3000	410	
	RS6R060BH	150	60*	21.8	30*	2.0 — 4.0	2750	260	

*Tc=25ºC

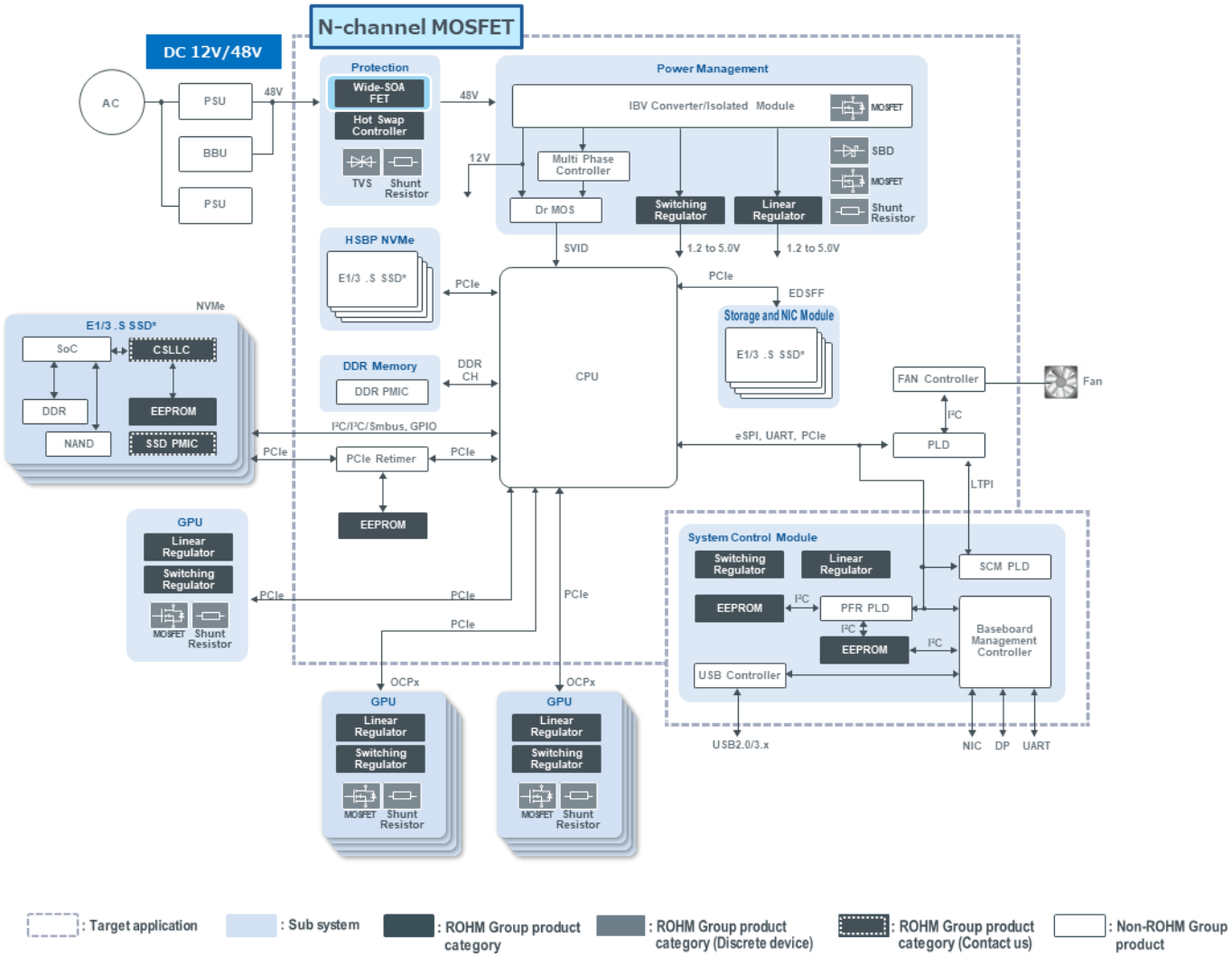
Server / DC/DC power module for communication equipment



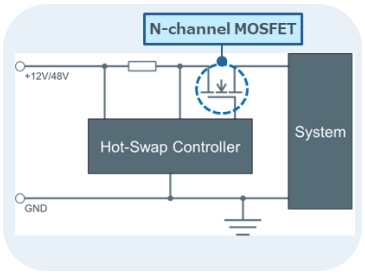
Recommended N-channel MOSFETs										
DC/DC converter										
Input/ Output Voltage	Circuit	Part Number	V_{DSS} (V)	I_D (A) Silicon limit	$R_{DS(on)}$ max. V_{GS}=10V (mΩ)	Q_g V_{GS}=4.5V V_{GS}=6V*	$V_{GS(th)}$	C_{iss} Typ.	C_{oss} Typ.	Size (mm)
12Vin 1.2Vout	High-Side Switch	RH6G040CG	40V	135	2.4	14.5	1.0 — 2.5	1910	1300	3.3 x 3.3 x 0.75 HSMT8
		RH6L040CH	60V	85	5.8	11.4*	2.0 — 4.0	1390	310	
	Low-Side Switch	RH6E040BG	30V	125	2.9	14.0	1.0 — 2.5	2300	950	
		RH6G040CG	40V	135	2.4	14.5	1.0 — 2.5	1910	1300	
48Vin 12Vout	High-Side Switch	RH6N040BH	80V	65	8.3	14.5*	2.0 — 4.0	1530	325	
		RH6P040BH	100V	40*	15.6	10.9*	2.0 — 4.0	1080	205	
		RH6R025BH	150V	25*	60	11.0*	2.0 — 4.0	1010	95	
	Low-Side Switch	RH6G040CG	40V	135	2.4	14.5	1.0 — 2.5	1910	1300	
		RH6L040BG	60V	65	7.1	9.2	1.0 — 2.5	1320	305	
		RH6N040BH	80V	65	8.3	14.5*	2.0 — 4.0	1530	325	
		RH6P040BH	100V	40*	15.6	10.9*	2.0 — 4.0	1080	205	

*Tc=25°C

Hot-Swap Controller for Servers



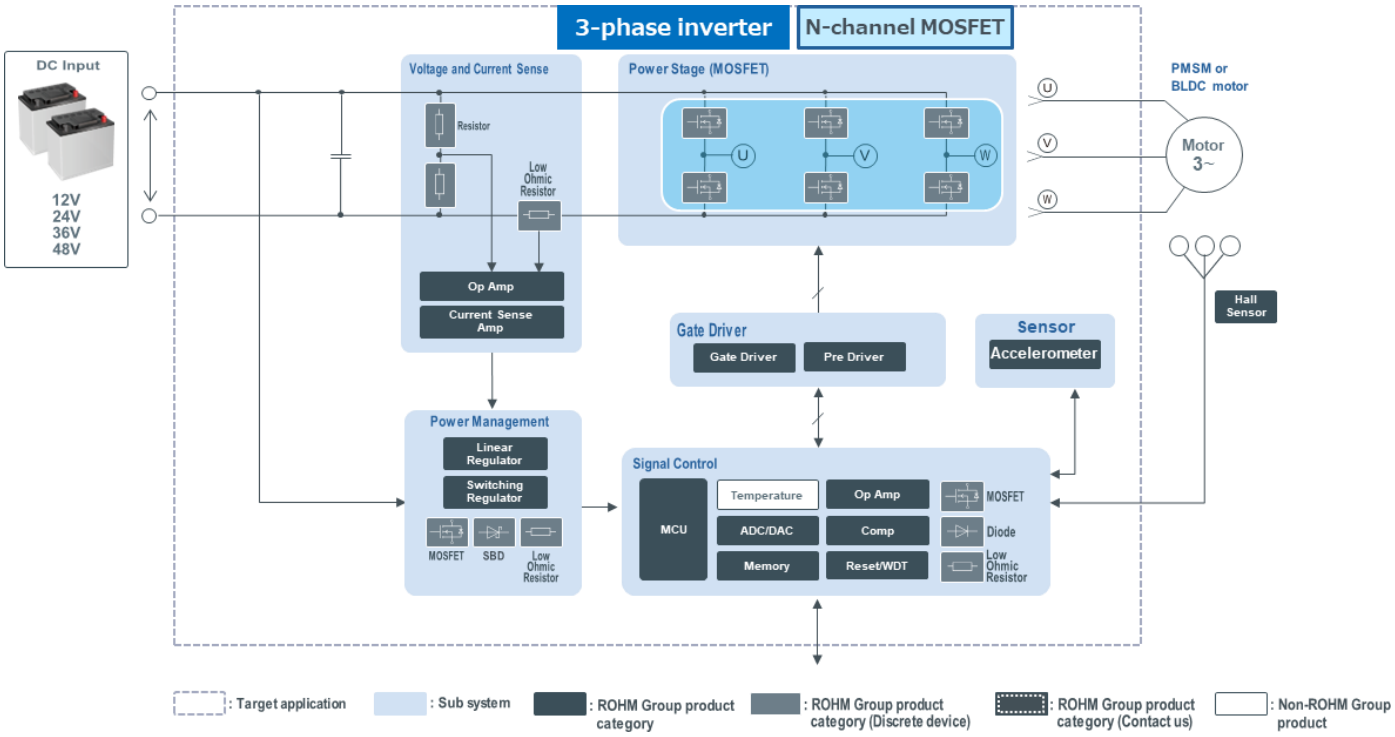
Hot-Swap Controller Circuit Diagram:



Recommended N-channel MOSFETs								
Hot-swap controller								
Battery Voltage	Part Number	V_{DSS} (V)	I_D (A) Silicon limit *Tc=25°C	$R_{DS(on)}$ max. V_{GS}=10V (mΩ)	SOA V_{DS}=12V*,48V (A)		Package	Size (mm)
					Pw=10ms	Pw=1ms		
12V system	RS7E200BG	30	390	0.67	25*	70*	DFN5060-8L	5.0 x 6.0 x 1.0
48V system	RY7P250BM	100	300	1.86	16	50	DFN8080-8L	8.0 x 8.0 x 1.0
	RJ2P17BBM*	100	290	2.2	15.3	41	TOLL	9.9 x 11.68 x 2.3
	RS7P200BM	100	200*	4.0	7.5	25	DFN5060-8L	5.0 x 6.0 x 1.0

Part Number*: Under development (specifications subject to change)

Industrial Motor Drive: 12–48V DC



Recommended N-channel MOSFETs							
Three-phase inverter							
Input Voltage	Type	Part Number	V_{DSS} (V)	I_D (A) Tc=25ºC	$R_{DS(on)}$ max. V_{GS}=10V (mΩ)	Package	Size (mm)
12Vin	Single	RS7E200BG	30	390*	0.67	DFN5060-8L	5.0 x 6.0 x1.0
	Dual (N-ch ×2)	HT8KA6	30	15	10.9	HSMT8	3.3 x 3.3 x 0.75
	Single	RB8G210CG*	40	210*	1.37	DFN3333-9L DSC	3.3 x 3.3 x 0.65
	Dual (N-ch ×2)	HT8KB6	40	15	17.2	HSMT8	3.3 x 3.3 x 0.75
24Vin	Single	RS7G200CG	40	410*	0.64	DFN5060-8L	5.0 x 6.0 x1.0
	Dual (N-ch ×2)	HP8KB7	40	24	8.0	HSOP8	5.0 x 6.0 x1.0
	Single	RH6L040CG	60	90*	5.6	HSMT8	3.3 x 3.3 x 0.75
	Dual (N-ch ×2)	HT8KC6	60	15	29	HSMT8	3.3 x 3.3 x 0.75
36Vin	Single	RS7L200CG	60	275*	1.39	DFN5060-8L	5.0 x 6.0 x1.0
	Dual (N-ch ×2)	HP8KC7	60	24	11.5	HSOP8	5.0 x 6.0 x1.0
	Single	RS7N200BH	80	230*	2.0	DFN5060-8L	5.0 x 6.0 x1.0
	Dual (N-ch ×2)	HP8KD6H*	80	18	32	HSOP8	5.0 x 6.0 x1.0
48Vin	Single	RS7P150BH	100	150	3.8	DFN5060-8L	5.0 x 6.0 x1.0
	Dual (N-ch ×2)	HP8KE7	100	24	19.6	HSOP8	5.0 x 6.0 x1.0
	Single	RS7R125CH	150	125	8.3	DFN5060-8L	5.0 x 6.0 x1.0
	Dual (N-ch ×2)	HP8KF7H	150	18.5	62	HSOP8	5.0 x 6.0 x1.0

Part Number*: Under development (specifications subject to change) *Silicon limit

N-channel MOSFET Application

Industrial Drives, Base Station, Motor control, AGV, Server Board, Notebook, Consumer, Battery, Onboard

5. Single type products

（Ta=25°C, unless otherwise specified）Lineup table: sorted in ascending order based on $R_{DS(on)}$ value

Single (V_{DSS}=20V)

Pin	6pin	8pin
(mm)	2.9x2.8x0.85	3.0x2.8x0.8
Package	TSMT6	TSMT8
V_{DSS}		
20V	RQ6C050UN 5.0A, **30mΩ** 1.5V drive Gen.1	RQ7C075UN 7.5A, **16mΩ** 1.5V drive Gen.1
		RQ7C065UN 6.5A, **22mΩ** 1.5V drive Gen.1

$R_{DS(on)}$ max at V_{GS}=4.5V

Part No.: Under development (No link. Specifications subject to change.)

Single (V_{DSS}=30V)

The data is sorted in ascending order of $R_{DS(on)}$.

Pin	7pin	8pin	6pin	3pin	6pin	8pin	8pin	8pin	8pin	8pin
(mm)	1.6x1.6	2.0x2.0	2.0x2.1	2.9x2.8	2.9x2.8	3.0x2.8	3.3x3.3	5.0x6.0	5.0x6.0	5.0x6.0
Package	HEML1616L7	HUML2020L8	TUMT6	TSMT3	TSMT6	TSMT8	HSMT8	SOP8	HSOP8	DFN5060-8L
V_{DSS}										
2.5V drive	RW4E075AJ 7.5A, **26mΩ** 2.5V drive Gen.5	RF4E100AJ 10A, **12.4mΩ** 2.5V drive Gen.5	RF6E045AJ 4.5A, **23.7mΩ** 2.5 drive Gen.5	RQ5E065AJ 6.5A, **18.1mΩ** 2.5V drive Gen.5	RQ6E080AJ 8A, **16.5mΩ** 2.5V drive Gen.5	RQ7E110AJ 11A, **9mΩ** 2.5V drive Gen.5	RQ3E180AJ 30A**, **4.5mΩ** 2.5V drive Gen.5	RS3E135BN 13.5A, **7.4mΩ** 4.5V drive Gen.4	RS6E120BG 270A*, **1.1mΩ** 4.5V drive Gen.6	RS7E200BG 390A*,**0.67mΩ** 4.5V drive Gen.6
	RW4E045AJ 4.5A, **40mΩ** 2.5V drive Gen.5	RF4E060AJ 6A, **37mΩ** 2.5V drive Gen.5	RF6E065BN 6.5A, **15.3mΩ** 4.5V drive Gen.4	RQ5E040AJ 4A, **37mΩ** 2.5V drive Gen.5	RQ6E050AJ 5A, **35mΩ** 2.5V drive Gen.5	RQ7E100XN 10A, **10.5mΩ** 4V drive Gen.3	RQ3E110AJ 24A**, **11.7mΩ** 2.5V drive Gen.5	RXH125N03 12.5A, **12mΩ** 4V drive Gen.3	RS1E350BN 80A**, **1.7mΩ** 4.5V drive Gen.4	
	RW4E065GN 6.5A, **22.5mΩ** 4.5V drive Gen.4	RF4E110BN 11A, **11.1mΩ** 4.5V drive Gen.4		RQ5E040TN 4A, **48mΩ** 2.5V drive Gen.1	RQ6E045TN 4.5A, **43mΩ** 2.5V drive Gen.1	RQ7E075XN 7.5A, **17mΩ** 4V drive Gen.3	RH6E040BG 125A*, **2.9mΩ** 4.5V drive Gen.6	RXH100N03 10A, **13mΩ** 4V drive Gen.3	RS1E350GN 80A**, **1.76mΩ** 4.5V drive Gen.4	
		RF4E110GN 11A, **11.3mΩ** 4.5V drive Gen.4		RQ5E030AJ 3A, **75mΩ** 2.5V drive Gen.5	RQ6E035TN 3.5A, **54mΩ** 2.5V drive Gen.1		RQ3E180BN 39A**, **3.9mΩ** 4.5V drive Gen.4	RS3E095BN 9.5A, **14.6mΩ** 4.5V drive Gen.4	RS1E321GN 80A**, **2.1mΩ** 4.5V drive Gen.4	
		RF4E080BN 8A, **17.6mΩ** 4.5V drive Gen.4		RQ5E025TN 2.5A, **92mΩ** 2.5V drive Gen.1	RQ6E085BN 8.5A, **14.4mΩ** 4.5V drive Gen.4		RQ3E180GN 39A**, **4.3mΩ** 4.5V drive Gen.4	RXH090N03 9A, **17mΩ** 4V drive Gen.3	RS6E122BG 155A*, **2.16mΩ** 4.5V drive Gen.6	
		RF4E080GN 8A, **17.6mΩ** 4.5V drive Gen.4		RQ5E070BN 7A, **16.1mΩ** 4.5V drive Gen.4	RQ6E055BN 5.5A, **25mΩ** 4.5V drive Gen.4		RQ3E160AD 16A, **4.5mΩ** 4.5V drive Gen.4	RXH070N03 7A, **28mΩ** 4V drive Gen.3	RS1E301GN 80A**, **2.2mΩ** 4.5V drive Gen.4	
		RF4E070GN 7A, **21.4mΩ** 4.5V drive Gen.4		RQ5E035BN 3.5A, **37mΩ** 4.5V drive Gen.4	RQ6E045BN 4.5A, **30mΩ** 4.5V drive Gen.4		RQ3E150BN 39A**, **5.3mΩ** 4.5V drive Gen.4		RS1E280BN 80A**, **2.3mΩ** 4.5V drive Gen.4	
		RF4E070BN 7A, **28.6mΩ** 4.5V drive Gen.4		RQ5E035XN 3.5A, **50mΩ** 4V drive Gen.3	RQ6E045SN 4.5A, **38mΩ** 4V drive Gen.1		RQ3E130BN 39A**, **6mΩ** 4.5V drive Gen.4		RS1E281BN 80A**, **2.3mΩ** 4.5V drive Gen.4	
30V				RQ5E025SN 2.5A, **70mΩ** 4V drive Gen.1	RQ6E040XN 4.0A, **50mΩ** 4V drive Gen.3		RQ3E150GN 39A**, **6.1mΩ** 4.5V drive Gen.4		RS1E280GN 80A**, **2.6mΩ** 4.5V drive Gen.4	
							RQ3E120GN 27A**, **8.8mΩ** 4.5V drive Gen.4		RS1E240BN 40A**, **3.2mΩ** 4.5V drive Gen.4	
							RQ3E120BN 21A**, **9.3mΩ** 4.5V drive Gen.4		RS1E240GN 72A**, **3.3mΩ** 4.5V drive Gen.4	
							RQ3E100BN 21A**, **10.4mΩ** 4.5V drive Gen.4		RS1E200BN 68A**, **3.9mΩ** 4.5V drive Gen.4	
							RQ3E100GN 21A**, **11.7mΩ** 4.5V drive Gen.4		RS1E200GN 57A**, **4.6mΩ** 4.5V drive Gen.4	
							RQ3E080BN 15A**, **15.2mΩ** 4.5V drive Gen.4		RS1E180BN 60A**, **4.9mΩ** 4.5V drive Gen.4	
							RQ3E080GN 18A**, **16.7mΩ** 4.5V drive Gen.4		RS1E170GN 40A**, **6.7mΩ** 4.5V drive Gen.4	
							RQ3E070BN 15A**, **27mΩ** 4.5V drive Gen.4		RS1E150GN 40A**, **8.8mΩ** 4.5V drive Gen.4	
									RS1E130GN 35A**, **11.7mΩ** 4.5V drive Gen.4	

$R_{DS(on)}$ max at V_{GS}=4.5V (2.5V drive)

$R_{DS(on)}$ max at V_{GS}=10V (4V, 4.5V drive)

Note) *IDSL(A)_Silicon limit, **Tc=25°C

Part No.: Under development (No link. Specifications subject to change.)

Single (V_{DSS}=40V)

The data is sorted in ascending order of $R_{DS(on)}$.

Pin	8pin	6pin	3pin	8pin	8pin	9pin	9pin
(mm)	2.0x2.0x0.6	2.0x2.1x0.77	2.9x2.8x0.85	3.0x2.8x0.8	3.3x3.3x0.75	3.3x3.3x1.0	3.3x3.3x0.65
Package	HUML2020L8	TUMT6	TSMT3	TSMT8	HSMT8	DFN3333-9L	DFN3333-9L DSC
V_{DSS}							
40V	RF4G100BG 10A, **14.2mΩ** 4.5V drive Gen.6	RF6G035BG 3.5A, **46mΩ** 4.5V drive Gen.6	RQ5G060BG 6.0A, **20.6mΩ** 4.5V drive Gen.6	RQ7G080BG 8.0A, **16.5mΩ** 4.5V drive Gen.6	RH6G040CG 135A*, **2.4mΩ** 4.5V drive Gen.7	RH8G210CG 210A*, **1.37mΩ** 4.5V drive Gen.7	RB8G210CG 210A*, **1.37mΩ** 4.5V drive Gen.7
					RH6G040CH 135A*, **2.5mΩ** 6V drive Gen.7	RH8G205CH 205A*, **1.42mΩ** 6V drive Gen.7	RB8G205CH 205A*, **1.42mΩ** 6V drive Gen.7
					RH6G040BG 95A*, **3.6mΩ** 4.5V drive Gen.6		

	8pin	8pin	8pin	3pin	3pin	3pin	3pin
	5.0x6.0x1.0	5.0x6.0x1.0	8.0x8.0x1.0	6.6x10.0x2.3	10.16x15.1x4.57	10.0x29.0x4.7	10.16x29.07x4.44
	HSOP8	DFN5060-8L	DFN8080-8L	TO-252	TO-263AB	TO-220FP	TO-220AB
							
40V	RS6G120CG 300A*, **0.9mΩ** 4.5V drive Gen.7	RS7G200CG 410A*, **0.64mΩ** 4.5V drive Gen.7	RY7G250CG 790A*, **0.27mΩ** 4.5V drive Gen.7	RD3G07BBG 150A*, **2.3mΩ** 4.5V drive Gen.6	RJ1G10BBG 280A*, **1.43mΩ** 4.5V drive Gen.6	RX2G10BBG 205A*, **1.47mΩ** 4.5V drive Gen.6	RX3G18BBG 270A*, **1.47mΩ** 4.5V drive Gen.6
	RS6G120CH 300A*, **0.91mΩ** 6V drive Gen.7	RS7G200CH 445A*, **0.65mΩ** 6V drive Gen.7	RY7G250CH 775A*, **0.28mΩ** 6V drive Gen.7	RD3G03BBG 65A*, **6.5mΩ** 4.5V drive Gen.6	RJ1G04BBG 130A*, **3.1mΩ** 4.5V drive Gen.6	RX2G07BBG 100A*, **3.0mΩ** 4.5V drive Gen.6	RX3G07BBG 130A*, **3.0mΩ** 4.5V drive Gen.6
	RS6G122CG 225A*, **1.19mΩ** 4.5V drive Gen.7						
	RS6G122CH 225A*, **1.2mΩ** 6V drive Gen.7						
	RS6G120BG 210A*, **1.34mΩ** 4.5V drive Gen.6						
	RS6G120BH 210A*, **1.38mΩ** 6V drive Gen.6						
	RS6G090CG 90A**, **3.1mΩ** 4.5V drive Gen.7						
	RS6G100BG 100A**, **3.4mΩ** 4.5V drive Gen.6						
	RS1G120MN 34A**, **16.2mΩ** 4.5V drive Gen.3						

$R_{DS(on)}$ max at V_{GS}=10V

Note) *IDSL(A)_Silicon limit, **Tc=25°C

Part No.: Under development (No link. Specifications subject to change.)

Single (V_{DSS}=45V)

The data is sorted in ascending order of $R_{DS(on)}$.

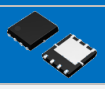
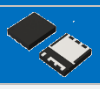
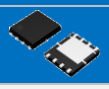
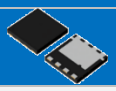
Pin	3pin	8pin	3pin
(mm)	2.9x2.8x0.85	5.0x6.0x1.75	6.6x10.0x2.3
Package	TSMT3	SOP8	TO-252
V_{DSS}			
2.5V drive	RQ5H030TN 3A, **67mΩ** 2.5V drive Gen.1	RSH070N05 7.0A, **25mΩ** 4V drive Gen.1	RD3H200SN 20A, **28mΩ** 4V drive Gen.1
45V	RQ5H025TN 2.5A, **130mΩ** 2.5V drive Gen.1		
	RQ5H020TN 2A, **180mΩ** 2.5V drive Gen.1		

$R_{DS(on)}$ max at V_{GS}=4.5V (2.5V drive)

$R_{DS(on)}$ max at V_{GS}=10V (4V drive)

Single (V_{DSS}=60V)

The data is sorted in ascending order of $R_{DS(on)}$.

Pin	8pin	6pin	3pin	8pin	8pin	9pin	9pin			
(mm)	2.0x2.0	2.0x2.1	2.9x2.8	3.0x2.8	3.3x3.3	3.3x3.3	3.3x3.3			
Package	HUML2020 L8	TUMT6	TSMT3	TSMT8	HSMT8	DFN3333-9L	DFN3333-9L DSC			
V_{DSS}										
60V	RF4L070BG 7A, **27mΩ** 4.5V drive Gen.6	RF6L025BG 2.5A, **91mΩ** 4.5V drive Gen.6	RQ5L045BG 4.5A, **32mΩ** 4.5V drive Gen.6	RQ7L055BG 5.5A, **29mΩ** 4.5V drive Gen.6	RH6L040CG 90A*, **5.6mΩ** 4.5V drive Gen.7	RH8L130CG 130A*, **3.8mΩ** 4.5V drive Gen.7	RB8L130CG 130A*, **3.8mΩ** 4.5V drive Gen.7			
			RQ5L030SN 3A, **85mΩ** 4V drive Gen.1		RH6L040CH 85A*, **5.8mΩ** 6V drive Gen.7	RH8L130CH 130A*, **3.9mΩ** 6V drive Gen.7	RB8L130CH 130A*, **3.9mΩ** 6V drive Gen.7			
			RQ5L020SN 2A, **170mΩ** 4V drive Gen.1		RH6L040BG 65A*, **7.1mΩ** 4.5V drive Gen.6					
					RQ3L070BG 20A**, **24.7mΩ** 4.5V drive Gen.6					
					RQ3L060BG 15.5A**, **38mΩ** 4.5V drive Gen.6					
60V	8pin	8pin	8pin	8pin	8pin	8pin	3pin	3pin	3pin	3pin
	5.0x6.0	5.0x6.0	5.0x6.0	5.2x6.15	5.2x6.15	8.0x8.0	6.6x10.0	10.16x15.1	10x29	10.16x29.07
	SOP8	HSOP8	DFN5060-8L	HSOP8	HSOP8-DC	DFN8080-8L	TO-252	TO-263AB	TO-220FP	TO-220AB
										
	RSH065N06 6.5A, **37mΩ** 4V drive Gen.1	RS6L120CG 195A*, **2.1mΩ** 4.5V drive Gen.7	RS7L200CG 275A*, **1.39mΩ** 4.5V drive Gen.7	RG5L245CH 245A*, **1.76mΩ** 6V drive Gen.7	RG6L245CH 245A*, **1.76mΩ** 6V drive Gen.7	RY7L250CG 535A*, **0.59mΩ** 4.5V drive Gen.7	RD3L07BBG 115A*, **3.9mΩ** 4.5V drive Gen.6	RJ1L10BBG 240A*, **1.85mΩ** 4.5V drive Gen.6	RX2L10BBG 180A*, **1.84mΩ** 4.5V drive Gen.6	RX3L18BBG 240A*, **1.84mΩ** 4.5V drive Gen.6
		RS6L120CH 190A*, **2.2mΩ** 6V drive Gen.7	RS7L200CH 270A*, **1.44mΩ** 6V drive Gen.7			RY7L250CH 520A*, **0.62mΩ** 6V drive Gen.7	RD3L03BBG 50A*, **11.3mΩ** 4.5V drive Gen.6	RJ1L04BBG 100A*, **4.6mΩ** 4.5V drive Gen.6	RX2L07BBG 80A*, **4.6mΩ** 4.5V drive Gen.6	RX3L07BBG 105A*, **4.6mΩ** 4.5V drive Gen.6
		RS6L120BG 150A*, **2.7mΩ** 4.5V drive Gen.6					RD3L220SN 22A, **26mΩ** 4V drive Gen.1			
		RS6L120BH 150A*, **2.7mΩ** 6V drive Gen.6					RD3L150SN 15A, **40mΩ** 4V drive Gen.1			
		RS6L122CG 140A*, **2.9mΩ** 4.5V drive Gen.7					RD3L080SN 8A, **80mΩ** 4V drive Gen.1			
		RS6L122CH 140A*, **3.0mΩ** 6V drive Gen.7					RD3L050SN 5A, **109mΩ** 4V drive Gen.1			
		RS6L090BG 90A**, **4.7mΩ** 4.5V drive Gen.6								
		RS6L090BH 90A**, **5.0mΩ** 6V drive Gen.6								

$R_{DS(on)}$ max at V_{GS}=4.5V (2.5V drive)

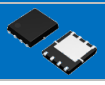
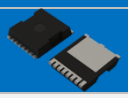
$R_{DS(on)}$ max at V_{GS}=10V (4V, 4.5V, 6V drive)

Note) *IDSL(A)_Silicon limit, **Tc=25°C

Part No.: Under development (No link. Specifications subject to change.)

Single (V_{DSS}=80V)

The data is sorted in ascending order of $R_{DS(on)}$.

Pin	8pin	9pin	9pin	8pin	8pin	8pin
(mm)	3.3x3.3x0.75	3.3x3.3x1.0	3.3x3.3x0.65	5.0x6.0x1.0	5.0x6.0x1.0	5.2x6.15x0.75
Package	HSMT8	DFN3333-9L	DFN3333-9L DSC	HSOP8	DFN5060-8L	HSOP8-DC
V_{DSS}						
80V	RH6N085CH 85A*, **6.1mΩ** 8V drive Gen.7	RH8N105BG 105A**, **5.0mΩ** 4.5V drive Gen.6	RB8N105BG 105A**, **5.0mΩ** 4.5V drive Gen.6	RS6N185CH 185A**, **2.3mΩ** 8V drive Gen.7	RS7N200CH 295A*, **1.43mΩ** 8V drive Gen.7	RG6N240CH 240A*, **1.83mΩ** 8V drive Gen.7
	RH6N040BG 65A*, **7.8mΩ** 4.5V drive Gen.6	RH8N105BH 105A**, **5.5mΩ** 6V drive Gen.6	RB8N105BH 105A**, **5.5mΩ** 6V drive Gen.6	RS6N120BH 135A*, **3.3mΩ** 6V drive Gen.6	RS7N200BH 230A*, **2.0mΩ** 6V drive Gen.6	RG6N210BH 210A*, **2.4mΩ** 6V drive Gen.6
	RH6N040BH 65A*, **8.3mΩ** 6V drive Gen.6				RS7N160BH 160A**, **2.6mΩ** 6V drive Gen.6	
80V	3pin	9pin	3pin	3pin		
	6.6x10.0x2.3	9.9x11.68x2.3	10.16x15.1x4.57	10.16x29.07x4.44		
	TO-252	TOLL	TO-263AB	TO-220AB		
						
	RD3N07BBH 105A*, **4.4mΩ** 6V drive Gen.6	RJ2N17BCH 450A*, **0.9mΩ** 8V drive Gen.7	RJ1N10BBH 235A*, **2.0mΩ** 6V drive Gen.6	RX3N10BBH 225A*, **2.2mΩ** 6V drive Gen.6		
		RJ2N17BBH 400A*, **1.16mΩ** 6V drive Gen.6	RJ1N04BBH 100A*, **5.3mΩ** 6V drive Gen.6	RX3N07BBH 100A*, **5.1mΩ** 6V drive Gen.6		

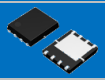
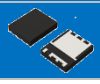
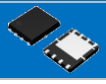
$R_{DS(on)}$ max at V_{GS}=10V

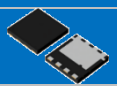
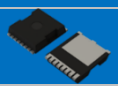
Note) *IDSL(A)_Silicon limit, **Tc=25°C

Part No.: Under development (No link. Specifications subject to change.)

Single (V_{DSS}=100V)

The data is sorted in ascending order of $R_{DS(on)}$.

Pin	8pin	3pin	8pin	9pin	9pin	8pin	8pin	8pin	8pin
(mm)	2.0x2.0	2.9x2.8	3.3x3.3	3.3x3.3	3.3x3.3	5.0x6.0	5.0x6.0	5.2x6.15	5.2x6.15
Package	HUML2020L8	TSMT3	HSMT8	DFN3333-9L	DFN3333-9L DSC	HSOP8	DFN5060-8L	HSOP8	HSOP8-DC
V_{DSS}									
100V	RF4P060BG 6A, **53mΩ** 4.5V drive Gen.6	RQ5P035BG 3.5A, **60mΩ** 4.5V drive Gen.6	RH6P040CH 65A*, **10.7mΩ** 8V drive Gen.7	RH8P085CH 85A*, **7.3mΩ** 8V drive Gen.7	RB8P085CH 85A*, **7.3mΩ** 8V drive Gen.7	RS6P120CH 140A**, **4.0mΩ** 6V drive Gen.7	RS7P200CH 205A*, **2.5mΩ** 8V drive Gen.7	RG5P180CH 180A**, **3.2mΩ** 8V drive Gen.7	RG6P180CH 180A**, **3.2mΩ** 8V drive Gen.7
		RQ5P010SN 1A, **520mΩ** 4V drive Gen.1	RQ3P300BH 39A**, **15.5mΩ** 6V drive Gen.6			RS6P122CH 105A**, **5.6mΩ** 8V drive Gen.7	RS7P150BH 150A**, **3.8mΩ** 6V drive Gen.6		
			RH6P040BH 40A**, **15.6mΩ** 6V drive Gen.6			RS6P100BG 100A**, **5.9mΩ** 4.5V drive Gen.6	RS7P200BM 200A**, **4.0mΩ** 10V drive Gen.6 WideSOA		
						RS6P100BH 100A**, **5.9mΩ** 6V drive Gen.6			
						RS1P600BH 60A**, **8.8mΩ** 6V drive Gen.6			
						RS6P060BH 60A**, **10.6mΩ** 6V drive Gen.6			

	8pin	3pin	9pin	3pin	3pin	3pin			
	8.0x8.0	6.6x10.0	9.9x11.68	10.16x15.1	10x29	10.16x29.07			
	DFN8080-8L	TO-252	TOLL	TO-263AB	TO-220FP	TO-220AB			
									
100V	RY7P250CH 390A*, **1.11mΩ** 6V drive Gen.7	RD3P07BBH 80A*, **7.7mΩ** 6V drive Gen.6	RJ2P17BCH 360A**, **1.41mΩ** 8V drive Gen.7	RJ1P10BBH 170A*, **3.0mΩ** 6V drive Gen.6	RX2P07CBH 85A*, **5.2mΩ** 6V drive Gen.6	RX3P10BBH 170A*, **3.3mΩ** 6V drive Gen.6			
	RY7P250BM 300A*, **1.86mΩ** 10V drive Gen.6 WideSOA	RD3P03BBH 35A**, **23mΩ** 6V drive Gen.6	RJ2P17BBH 295A*, **2.0mΩ** 6V drive Gen.6	RJ1P07CBH 120A*, **5.1mΩ** 6V drive Gen.6	RX2P06BBH 65A**, **8.4mΩ** 6V drive Gen.6	RX3P07CBH 120A*, **5.2mΩ** 6V drive Gen.6			
		RD3P200SN 20A, **46mΩ** 4V drive Gen.1	RJ2P17BBM 290A*, **2.2mΩ** 10V drive Gen.6 WideSOA	RJ1P04BBH 80A*, **8.8mΩ** 6V drive Gen.6		RX3P07BBH 80A*, **8.4mΩ** 6V drive Gen.6			
		RD3P175SN 17.5A, **105mΩ** 4V drive Gen.1	RJ2P14BBH 225A*, **2.8mΩ** 6V drive Gen.6						
		RD3P100SN 10A, **133mΩ** 4V drive Gen.1							
		RD3P050SN 5.0A, **190mΩ** 4V drive Gen.1							

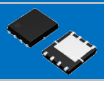
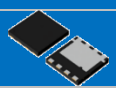
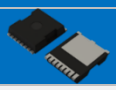
$R_{DS(on)}$ max at V_{GS}=10V

Note) *IDSL(A)_Silicon limit, **Tc=25°C

Part No.: Under development (No link. Specifications subject to change.)

Single (V_{DSS}=150V)

The data is sorted in ascending order of $R_{DS(on)}$.

Pin	8pin	9pin	9pin	8pin	8pin	8pin
(mm)	3.3x3.3x0.75	3.3x3.3x1.0	3.3x3.3x0.65	5.0x6.0x1.0	5.0x6.0x1.0	8.0x8.0x1.0
Package	HSMT8	DFN3333-9L	DFN3333-9L DSC	HSOP8	DFN5060-8L	DFN8080-8L
V_{DSS}						
150V	RH6R040CH 40A**, **38mΩ** 8V drive Gen.7	RH8R045CH 45A*, **26mΩ** 8V drive Gen.7	RB8R045CH 45A*, **26mΩ** 8V drive Gen.7	RS6R085CH 85A**, **13.9mΩ** 8V drive Gen.7	RS7R125CH 125A**, **8.3mΩ** 8V drive Gen.7	RY7R250CH 250A**, **4mΩ** 8V drive Gen.7
	RH6R025BH 25A**, **60mΩ** 6V drive Gen.6			RS6R060BH 60A**, **21.8mΩ** 6V drive Gen.6		
				RS6R035BH 35A**, **41mΩ** 6V drive Gen.6		
	3pin	9pin	3pin	3pin	3pin	
	6.6x10.0x2.3	9.9x11.68x2.3	10.16x15.1x4.57	10.0x29.0x4.7	10.16x29.07x4.44	
	TO-252	TOLL	TO-263AB	TO-220FP	TO-220AB	
						
150V	RD3R05BBH 50A**, **29mΩ** 6V drive Gen.6	RJ2R17BCH 205A**, **4.3mΩ** 8V drive Gen.7	RJ1R10BBH 105A**, **8.2mΩ** 6V drive Gen.6	RX2R03BBH 35A**, **29mΩ** 6V drive Gen.6	RX3R10BBH 105A**, **8.8mΩ** 6V drive Gen.6	
	RD3R02BBH 20A**, **81mΩ** 6V drive Gen.6		RJ1R04BBH 40A**, **27mΩ** 6V drive Gen.6		RX3R05BBH 50A**, **29mΩ** 6V drive Gen.6	

$R_{DS(on)}$ max at V_{GS}=10V

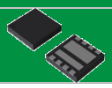
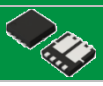
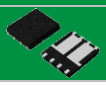
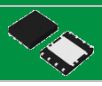
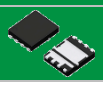
Note) *IDSL(A)_Silicon limit, **Tc=25°C

Part No.: Under development (No link. Specifications subject to change.)

6. Dual type products

Dual (V_{DSS}=30V, 40V, 45V)

The data is sorted in ascending order of $R_{DS(on)}$.

Pin	8pin	8pin	10pin	8pin	8pin	8pin	9pin	9pin
(mm)	2.0x2.0x0.6	3.0x2.8x0.8	3.0x3.0x0.6	3.3x3.3x0.75	5.0x6.0x1.75	5.0x6.0x1.0	5.0x6.0x1.0	5.0x6.0x1.0
Package	HUML2020L8	TSMT8	HSML3030L10	HSMT8	SOP8	HSOP8	HSOP8	HSOP8
V_{DSS}								
2.5V drive	UT6K3 5.5A, **42mΩ** 2.5V drive Gen.5	QH8KA4 9A, **17mΩ** 2.5V drive Gen.5	HS8K1 10/11A, **14.6/11.8mΩ** 4.5V drive Gen.4	HT8KA6 15A**, **10.9mΩ** 4.5V drive Gen.4	SH8KA7 15A, **9.3mΩ** 4.5V drive Gen.4		HP8KA1 14A, **5mΩ** 4.5V drive Gen.4	HP8K24 27/80A**, **8.8/3.0mΩ** 4.5V drive Gen.4
		QH8KA3 9A, **16mΩ** 4.5V drive Gen.4	HS8K11 7/11A, **17.9/13.3mΩ** 4.5V drive Gen.4/5	HT8KA5 12A**, **16.4mΩ** 4.5V drive Gen.4	SH8KA4 9A, **21.4mΩ** 4.5V drive Gen.4			HP8K22 27/57A**, **8.8/4.6mΩ** 4.5V drive Gen.4
30V		QH8K13 6A, **28mΩ** 4V drive Gen.3			SH8KA2 8A, **28.0mΩ** 4.5V drive Gen.4			
		QH8KA2 4.5A, **35mΩ** 4.5V drive Gen.4			SH8K12 5A, **42mΩ** 4V drive Gen.3			
		QH8K11 3.5A, **50mΩ** 4V drive Gen.3			SH8KA1 4.5A, **80mΩ** 4.5V drive Gen.4			
		QH8KA1 4.5A, **73mΩ** 4.5V drive Gen.4			SH8K11 3.5A, **98mΩ** 4V drive Gen.3			
	UT6KB5 5A, **48mΩ** 4.5V drive Gen.6	QH8KB6 8A, **17.7mΩ** 4.5V drive Gen.6		HT8KB6 15A**, **17.2mΩ** 4.5V drive Gen.6	SH8KB7 13.5A, **8.4mΩ** 4.5V drive Gen.6	HP8KB7 24A**, **8mΩ** 4.5V drive Gen.6		
40V		QH8KB5 7.5A, **44mΩ** 4.5V drive Gen.6		HT8KB5 12A**, **47mΩ** 4.5V drive Gen.6	SH8KB6 8.5A, **19.4mΩ** 4.5V drive Gen.6	HP8KB6 24A**, **15.7mΩ** 4.5V drive Gen.6		
					SH8KB5 4.5A, **55mΩ** 4.5V drive Gen.6	HP8KB5 16.5A**, **46mΩ** 4.5V drive Gen.6		
45V		QH8K21 4A, **53mΩ** 4V drive Gen.1						

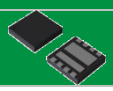
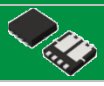
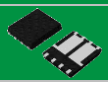
$R_{DS(on)}$ max at V_{GS}=4.5V (2.5V drive)

$R_{DS(on)}$ max at V_{GS}=10V (4V, 4.5V drive)

Note) **Tc=25°C, Part No.: Under development (No link. Specifications subject to change.)

Dual (V_{DSS}=60V, 80V, 100V, 150V)

The data is sorted in ascending order of $R_{DS(on)}$.

Pin	8pin	8pin	10pin	8pin	8pin	8pin
(mm)	2.0x2.0x0.6	3.0x2.8x0.8	3.0x3.0x0.6	3.3x3.3x0.75	5.0x6.0x1.75	5.0x6.0x1.0
Package	HUML2020L8	TSMT8	HSML3030L10	HSMT8	SOP8	HSOP8
V_{DSS}						
60V	UT6KC5 3.5A, **95mΩ** 4.5V drive Gen.6	QH8KC6 5.5A, **30mΩ** 4.5V drive Gen.6		HT8KC6 15A**, **29mΩ** 4.5V drive Gen.6	SH8KC7 10.5A, **12.4mΩ** 4.5V drive Gen.6	HP8KC7 24A**, **11.5mΩ** 4.5V drive Gen.6
		QH8KC5 3A, **90mΩ** 4.5V drive Gen.6		HT8KC5 10A**, **90mΩ** 4.5V drive Gen.6	SH8KC6 6.5A, **32mΩ** 4.5V drive Gen.6	HP8KC6 23A**, **27mΩ** 4.5V drive Gen.6
					SH8KC5 3.5A, **95mΩ** 4.5V drive Gen.6	HP8KC5D 12A**, **90mΩ** 4.5V drive Gen.6 High-ESD
						HP8KC5 12A**, **90mΩ** 4.5V drive Gen.6
80V				HT8KD6H 15A**, **33mΩ** 6V drive Gen.6		HP8KD6H 18A**, **32mΩ** 6V drive Gen.6
100V	UT6KE5 2A, **207mΩ** 4.5V drive Gen.6	QH8KE6 4A, **56mΩ** 4.5V drive Gen.6	HS8KE6H 6.5A, **43mΩ** 8V drive Gen.7	HT8KE6 13A**, **57mΩ** 4.5V drive Gen.6	SH8KE7 8A, **20.9mΩ** 4.5V drive Gen.6	HP8KE7 24A**, **19.6mΩ** 4.5V drive Gen.6
		QH8KE5 2A, **202mΩ** 4.5V drive Gen.6	HS8KE5 4.5A, **59mΩ** 4.5V drive Gen.6	HT8KE6D 12.5A**, **60mΩ** 6V drive Gen.6 High-ESD	SH8KE6 4.5A, **58mΩ** 4.5V drive Gen.6	HP8KE6 17A**, **54mΩ** 4.5V drive Gen.6
		QH8K51 2A, **325mΩ** 4V drive Gen.1		HT8KE6H 12.5A**, **60mΩ** 6V drive Gen.6	SH8KE5 2.5A, **200mΩ** 4.5V drive Gen.6	HP8KE5 8.5A**, **193mΩ** 4.5V drive Gen.6
				HT8KE5 7A**, **193mΩ** 4.5V drive Gen.6		
				HT8KE5H 6.5A**, **210mΩ** 6V drive Gen.6		
150V				HT8KF6H 7A**, **214mΩ** 6V drive Gen.6		HP8KF7H 18.5A**, **62mΩ** 6V drive Gen.6

$R_{DS(on)}$ max at V_{GS}=10V

Note) **Tc=25°C, Part No.: Under development (No link. Specifications subject to change.)

7. Nomenclature of the Part Number（New Products）

Single MOSFETs

R S 6 E 1 2 0 B G

ROHM

Package

D3 = TO-252
F4 = DFN2020-8S (HUML2020L8)
F6 = SOT-363T (TUMT6)
J1 = TO-263AB (LPTL)
J2 = TOLL (TOLL-9LSATAC)
Q3 = HSMT8
Q5 = SOT-346T (TSMT3)
Q6 = SOT-457T (TSMT6)
Q7 = TSMT8
S1 = HSOP8
S3 = SOP8
W4 = DFN1616-7T (HEML1616L7)
X2 = TO-220FP (TO-220FM)
X3 = TO-220AB

Cu-Clip type
B8 = DFN3333-9L DSC Source-Down
H8 = DFN3333-9L Source-Down
H6 = HSMT8
G5 = HSOP
G6 = HSOP8-DC
S6 = HSOP8
S7 = DFN5060-8L
Y7 = DFN8080-8L

V_{DSS}

E = 30V
G = 40V
L = 60V
N = 80V
P = 100V
R = 150V

I_D e.g.)

010 = 1.0A
: :
100 = 10A
: :
250 = 25A
01B = 10A
: :
03B = 35A
04B = 40A
: :
07B, 07C = 70A
10B = 105A
12B = 120A
18B = 180A

Cu-Clip type
040 = 40A
: :
200 = 200A

Specification / Drive voltage

N-channel
AJ = Gen.5 N-ch / 2.5V
BG = Gen.6 N-ch / 4.5V
BH = Gen.6 N-ch / 6V
BM = Gen.6 N-ch (Wide-SOA) / 10V
CG = Gen.7 N-ch / 4.5V
CH = Gen.7 N-ch / 6V, 8V
UN = Gen.1 N-ch / 1.5V
XN = Gen.3 N-ch / 4V

P-channel
AT = Gen.5 P-ch / 4.5V, 6.0V
BC = Gen.5 P-ch / 1.8V
DT = Gen.6 P-ch / 4.5V

Dual MOSFETs

Package
HP8 = HSOP8
HS8 = HSML3030L10
HS8 = DFN3333-9DC (HSML3333L9)
HT8 = HSMT8
QH8 = TSMT8
SH8 = SOP8
UT6 = DFN2020-8D (HUML2020L8)

Pin quantity

Polarity
J = P-ch, dual
K = N-ch, dual
M = N-ch + P-ch

V_{DSS}
A = 30V
B = 40V
C = 60V
D = 80V
E = 100V
F = 150V

Serial No.

Specification
D = ESD protection
H = High drive / 6V Drive

Part Number Information Link:

https://fscdn.rohm.com/en/products/databook/explanation/discrete/transistor/common/transistor_part_number_information_an-e.pdf

Contact Information

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